

### DN8B20KC 20V/0.8A N Channel Small Signal MOSFET

### **General description**

20V/0.8A N Channel Small Signal MOSFET

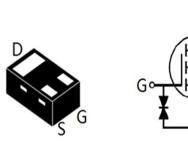
#### Features:

- Low RDS(on) @VGS=4.5V
- 2.5V Logic Level Control
- N Channel SOT-883 Package
- **ESD Protection**
- Pb-Free, RoHS Compliant

#### **Applications**

- LED Lighting Application, ON/OFF switch
- Networking

| V <sub>(BR)DSS</sub> | Rds(on) Typ  | I <sub>D</sub> Max |  |
|----------------------|--------------|--------------------|--|
| 20V                  | 200mΩ @4.5V  | 0.04               |  |
|                      | 220mΩ @ 3.3V | 0.8A               |  |



**SOT-883** 

### Absolute Maximum Ratings (TA=25°Cunless otherwise noted)

| Symbol  | Parameter                           | Rating               | Unit       |      |  |  |
|---|-------------------------------------|----------------------|------------|------|--|--|
| Common Ratings (Ta=25°C Unless Otherwise Noted) |                                     |                      |            |      |  |  |
| V <sub>GS</sub>                                 | Gate-Source Voltage                 | ±8                   | V          |      |  |  |
| V <sub>(BR)DSS</sub>                            | Drain-Source Breakdown Voltage      |                      | 20         | V    |  |  |
| TJ  | Maximum Junction Temperature        |                      | 150        | °C   |  |  |
| Тѕтс  | Storage Temperature Range           |                      | -50 to 150 | °C   |  |  |
| Mounted on Large Heat Sink                      |                                     |                      |            |      |  |  |
| I <sub>DM</sub>                                 | Pulse Drain Current Tested①         | T <sub>A</sub> =25°C | 3.2        | А    |  |  |
| lο  | Continuous Drain Current            | T <sub>A</sub> =25°C | 0.8        | А    |  |  |
|   |                                     | T <sub>A</sub> =70°C | 0.65       |      |  |  |
| Po  | Maximum Power Dissipation           | T <sub>A</sub> =25°C | 0.3        | W    |  |  |
|   |                                     | T <sub>A</sub> =70°C | 0.2        |      |  |  |
| R JA  | Thermal Resistance Junction-Ambient |                      | 400        | °C/W |  |  |

Page 1 of 6 www.doeshare.net

# DN8B20KC



| Symbol  | Parameter   | Condition   | Min  | Тур  | Max | Unit |  |
|---|---|---|------|------|-----|------|--|
| Static Electrical Characteristics @ T <sub>J</sub> = 25°C (unless otherwise stated) |   |   |      |      |     |      |  |
| V <sub>(BR)DSS</sub>  | Drain-Source Breakdown Voltage                            | Vgs=0V Id=250μA   | 20   |      |     | V    |  |
| IDSS  | Zero Gate Voltage Drain Current(T <sub>A</sub> =25℃)      | V <sub>D</sub> s=20V, V <sub>G</sub> s=0V                               |      |      | 1   | μА   |  |
|   | Zero Gate Voltage Drain<br>Current(T <sub>A</sub> =125°C) | V <sub>DS</sub> =16V, V <sub>GS</sub> =0V                               |      |      | 100 | uA   |  |
| Igss  | Gate-Body Leakage Current                                 | Vgs=±8V, Vps=0V   |      |      | ±10 | uA   |  |
| V <sub>GS(TH)</sub>   | Gate Threshold Voltage                                    | Vps=Vgs, Ip=250μA   | 0.35 | 0.6  | 1.0 | V    |  |
| R <sub>DS(ON)</sub>   | Drain-Source On-State Resistance②                         | Vgs=4.5V, ID=0.5A   |      | 200  | 300 | mΩ   |  |
| R <sub>DS(ON)</sub>   | Drain-Source On-State Resistance②                         | Vgs=3.3V, ID=0.3A   |      | 220  | 350 | mΩ   |  |
| R <sub>DS(ON)</sub>   | Drain-Source On-State Resistance②                         | Vgs=2.5V, ID=0.2A   |      | 250  | 400 | mΩ   |  |
|   | Electrical Characteristics @ T <sub>J</sub> = 25°C (      | unless otherwise state  | d)   | l    | ı   | ı    |  |
| Ciss  | Input Capacitance   | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,<br>f=1MHz                    |      | 36   |     | pF   |  |
| Coss  | Output Capacitance  |   |      | 9.3  |     | pF   |  |
| Crss  | Reverse Transfer Capacitance                              |   |      | 6.8  |     | pF   |  |
| Qg  | Total Gate Charge   | V <sub>DS</sub> =10V<br>I <sub>D</sub> =0.5A,<br>V <sub>GS</sub> =4.5V  |      | 0.8  |     | nC   |  |
| Qgs   | Gate Source Charge  |   |      | 0.11 |     | nC   |  |
| Q <sub>gd</sub>   | Gate Drain Charge   | ]   |      | 0.18 |     | nC   |  |
| Switching Characteristics   |   |   |      |      |     |      |  |
| t <sub>d(on)</sub>  | Turn on Delay Time  | V <sub>DD</sub> =10V,<br>I <sub>D</sub> =0.5A,<br>R <sub>G</sub> =3.3Ω, |      | 7    |     | ns   |  |
| tr  | Turn on Rise Time   |   |      | 10   |     | ns   |  |
| t <sub>d(off)</sub>   | Turn Off Delay Time                                       |   | -    | 35   |     | ns   |  |
| <b>t</b> f  | Turn Off Fall Time  | - Vgs=4.5V  |      | 14   |     | ns   |  |
| Source Drain Diode Characteristics  |   |   |      |      |     |      |  |
| SD  | Source drain current(Body Diode)                          | T <sub>A</sub> =25℃   |      |      | 0.5 | А    |  |
| V <sub>SD</sub>   | Forward on voltage②                                       | Tj=25℃, IsD=0.3A,<br>VGS=0V   |      | 0.74 | 1.2 | ٧    |  |

#### Notes:

Page 2 of 6 www.doeshare.net

① Pulse width limited by maximum allowable junction temperature
 ② Pulse test; Pulse width≤300μs, duty cycle≤2%



## **Typical Characteristics**

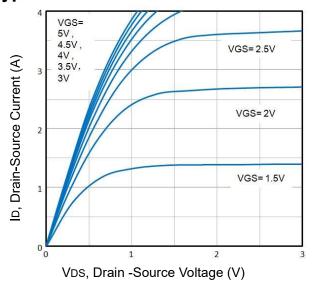
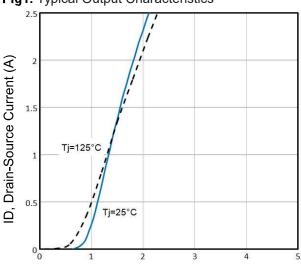
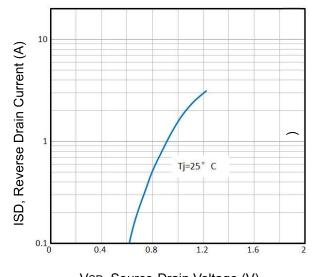


Fig1. Typical Output Characteristics



VGS, Gate -Source Voltage (V)

Fig3. Typical Transfer Characteristics



Vsp, Source-Drain Voltage (V)

Fig5. Typical Source-Drain Diode Forward Voltage

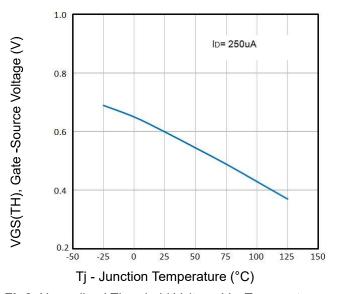


Fig2. Normalized Threshold Voltage Vs. Temperature

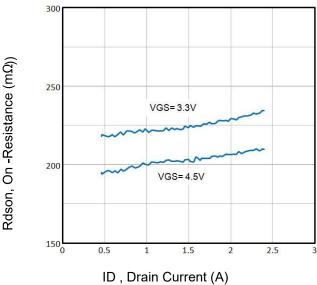
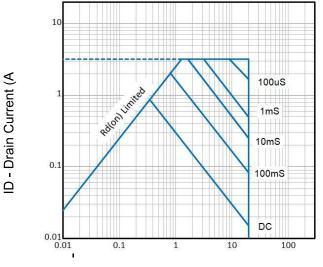


Fig4. On-Resistance vs. Drain Current and Gate



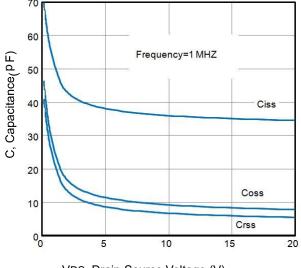
VDS, Drain -Source Voltage (V)

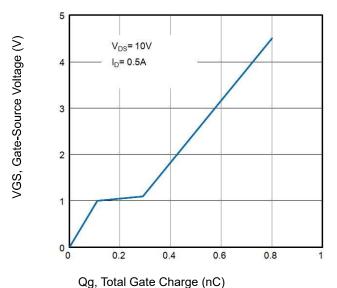
Fig6. Maximum Safe Operating Area

www.doeshare.net Page 3 of 6



## **Typical Characteristics**





VDS, Drain-Source Voltage (V)

Fig8. Typical Gate Charge Vs. Gate-Source Voltage

Fig7. Typical Capacitance Vs. Drain-Source Voltage

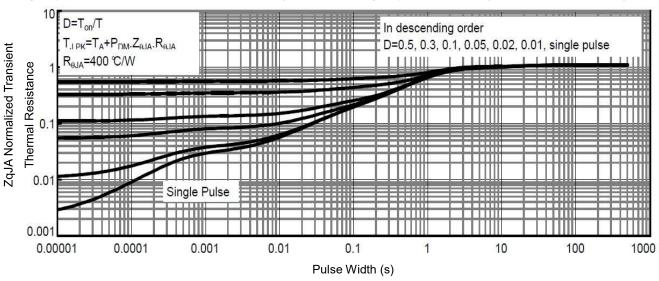


Fig9. Normalized Maximum Transient Thermal Impedance

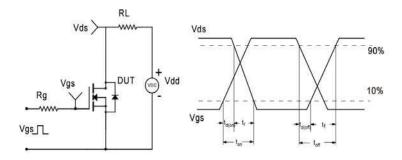
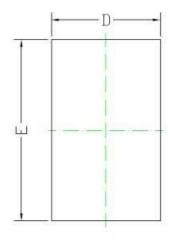


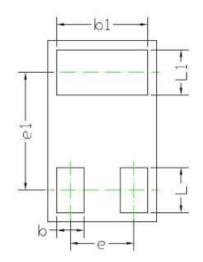
Fig10. Switching Time Test Circuit and waveforms

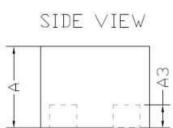
www.doeshare.net Page 4 of 6



# SOT-883 Package outline







| S                     |                       | COMMON |      |  |
|-----------------------|-----------------------|--------|------|--|
| S<br>M<br>B<br>D<br>L | DIMENSIONS MILLIMETER |        |      |  |
| -                     | MIN                   | NDM.   | MAX  |  |
| Α                     | 0.40                  | 0.45   | 0.50 |  |
| A3                    | 0.127 BSC             |        |      |  |
| D                     | 0,55                  | 0.60   | 0.65 |  |
| E                     | 0.95                  | 1.00   | 1.05 |  |
| 6                     | 0.35 BSC              |        |      |  |
| e1                    | 0.65 BSC              |        |      |  |
| b                     | 0.13                  | 0.15   | 0.18 |  |
| b1                    | 0.45                  | 0.50   | 0.55 |  |
| L                     | 0.20                  | 0.25   | 0.30 |  |
| L1                    | 0.20                  | 0.25   | 0.30 |  |

www.doeshare.net Page **5** of **6** 



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PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7
SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6
C3M0021120D DMN13M9UCA6-7 BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IRF40SC240ARMA1
IPS60R1K0PFD7SAKMA1